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# MOSFET

Metal Oxide Semiconductor Field Effect Transistor

## CoolMOS™ C6 600V

600V CoolMOS™ C6 Power Transistor  
IPU60R2K0C6

## Data Sheet

Rev. 2.2  
Final

Industrial & Multimarket



## 1 Description

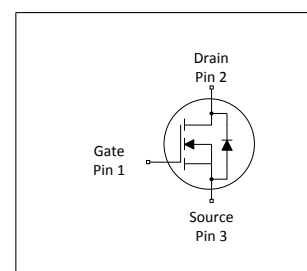
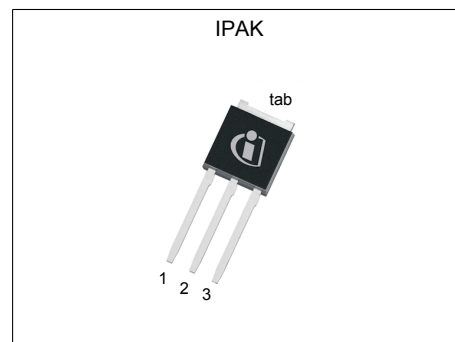
CoolMOS™ is a revolutionary technology for high voltage power MOSFETs, designed according to the superjunction (SJ) principle and pioneered by Infineon Technologies. CoolMOS™ C6 series combines the experience of the leading SJ MOSFET supplier with high class innovation. The resulting devices provide all benefits of a fast switching SJ MOSFET while not sacrificing ease of use. Extremely low switching and conduction losses make switching applications even more efficient, more compact, lighter and cooler.

## Features

- Extremely low losses due to very low FOM  $R_{ds(on)} \cdot Q_g$  and  $E_{oss}$
- Very high commutation ruggedness
- Easy to use/drive
- Pb-free plating, Halogen free mold compound
- Qualified for industrial grade applications according to JEDEC (J-STD20 and JESD22)

## Applications

PFC stages, hard switching PWM stages and resonant switching PWM stages for e.g. PC Silverbox, Adapter, LCD & PDP TV, Lighting, Server, Telecom, UPS.



**Table 1 Key Performance Parameters**

Parameter	Value	Unit
$V_{DS} @ T_{j,max}$	650	V
$R_{DS(on),max}$	2	$\Omega$
$Q_g,typ$	6.7	nC
$I_D,pulse$	6	A
$E_{oss} @ 400V$	0.76	$\mu J$
Body diode $di/dt$	500	A/ $\mu s$

Type / Ordering Code	Package	Marking	Related Links
IPU60R2K0C6	PG-TO 251	6R2K0C6	see Appendix A

**Table of Contents**

Description .....	2
Table of Contents .....	3
Maximum ratings .....	4
Thermal characteristics .....	5
Electrical characteristics .....	6
Electrical characteristics diagrams .....	8
Test Circuits .....	12
Package Outlines .....	13
Appendix A .....	14
Revision History .....	15
Disclaimer .....	15

## 2 Maximum ratings

at  $T_j = 25^\circ\text{C}$ , unless otherwise specified

**Table 2 Maximum ratings**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current <sup>1)</sup>	$I_D$			2.4	A	$T_C = 25^\circ\text{C}$
				1.5		$T_C = 100^\circ\text{C}$
Pulsed drain current <sup>2)</sup>	$I_{D,pulse}$			6	A	$T_C = 25^\circ\text{C}$
Avalanche energy, single pulse	$E_{AS}$			11	mJ	$I_D = 0.4\text{A}$ , $V_{DD} = 50\text{V}$ (see table 10)
Avalanche energy, repetitive	$E_{AR}$			0.06	mJ	$I_D = 0.4\text{A}$ , $V_{DD} = 50\text{V}$
Avalanche current, repetitive	$I_{AR}$			0.4	A	
MOSFET dv/dt ruggedness	dv/dt			50	V/ns	$V_{DS} = 0 \dots 480\text{V}$
Gate source voltage	$V_{GS}$	-20		20	V	static
		-30		30		AC ( $f > 1\text{ Hz}$ )
Operating and storage temperature	$T_j, T_{stg}$	-55		150	$^\circ\text{C}$	
Continuous diode forward current	$I_S$			2.1	A	$T_C = 25^\circ\text{C}$
Diode pulse current	$I_{S,pulse}$			6	A	$T_C = 25^\circ\text{C}$
Reverse diode dv/dt <sup>3)</sup>	dv/dt			15	V/ns	$V_{DS} = 0 \dots 480\text{V}$ , $I_{SD} \leq I_D$ ,
Maximum diode commutation speed	di <sub>f</sub> /dt			500	A/ $\mu\text{s}$	$T_j = 25^\circ\text{C}$ (see table 8)
Power dissipation	$P_{tot}$			22.3		$T_C = 25^\circ\text{C}$

<sup>1)</sup> Limited by  $T_{j,max}$ . Maximum duty cycle  $D=0.75$

<sup>2)</sup> Pulse width  $t_p$  limited by  $T_{j,max}$

<sup>3)</sup> Identical low side and high side switch with identical  $R_\theta$

### 3 Thermal characteristics

**Table 3 Thermal characteristics IPAK**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	$R_{thJC}$			5.6	°C/W	
Thermal resistance, junction - ambient <sup>1)</sup>	$R_{thJA}$			62	°C/W	SMD version, device on PCB, minimal footprint
			35			SMD version, device on PCB, 6cm <sup>2</sup> cooling area
Soldering temperature, wave- & reflowsoldering allowed	$T_{sold}$			260	°C	reflow MSL

<sup>1)</sup> Device on 40mm\*40mm\*1.5mm one layer epoxy PCB FR4 with 6cm<sup>2</sup> copper area (thickness 70µm) for drain connection. PCB is vertical without air stream cooling.

## 4 Electrical characteristics

at  $T_j = 25^\circ\text{C}$ , unless otherwise specified

**Table 4 Static characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	600			V	$V_{GS} = 0V, I_D = 0.25\text{mA}$
Gate threshold voltage	$V_{GS(th)}$	2.5	3	3.5	V	$V_{DS} = V_{GS}, I_D = 0.1\text{mA}$
Zero gate voltage drain current	$I_{DSS}$			1	$\mu\text{A}$	$V_{DS} = 600V, V_{GS} = 0V, T_j = 25^\circ\text{C}$
			10			$V_{DS} = 600V, V_{GS} = 0V, T_j = 150^\circ\text{C}$
Gate-source leakage current	$I_{GSS}$			100	nA	$V_{GS} = 20V, V_{DS} = 0V$
Drain-source on-state resistance	$R_{DS(on)}$		1.800	2	$\Omega$	$V_{GS} = 10V, I_D = 0.8A, T_j = 25^\circ\text{C}$
			4.680			$V_{GS} = 10V, I_D = 0.76A, T_j = 150^\circ\text{C}$
Gate resistance	$R_G$		12		$\Omega$	$f = 1\text{MHz}$ , open drain

**Table 5 Dynamic characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	$C_{iss}$		140		pF	$V_{GS} = 0V, V_{DS} = 100V, f = 1\text{MHz}$
Output capacitance	$C_{oss}$		12		pF	
Effective output capacitance, energy related <sup>1)</sup>	$C_{o(er)}$		8.5		pF	$V_{GS} = 0V, V_{DS} = 0 \dots 480V$
Effective output capacitance, time related <sup>2)</sup>	$C_{o(tr)}$		30		pF	$I_D = \text{constant}, V_{GS} = 0V, V_{DS} = 0 \dots 480V$
Turn-on delay time	$t_{d(on)}$		7		ns	$V_{DD} = 400V, V_{GS} = 10V, I_D = 0.9A, R_G = 12.2\Omega$ (see table 9)
Rise time	$t_r$		7		ns	
Turn-off delay time	$t_{d(off)}$		30		ns	
Fall time	$t_f$		50		ns	

**Table 6 Gate charge characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	$Q_{gs}$		0.8		nC	$V_{DD} = 480V, I_D = 0.9A, V_{GS} = 0 \text{ to } 10V$
Gate to drain charge	$Q_{gd}$		3.6		nC	
Gate charge total	$Q_g$		6.7		nC	
Gate plateau voltage	$V_{plateau}$		5.4		V	

<sup>1)</sup>  $C_{o(er)}$  is a fixed capacitance that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{(BR)DSS}$

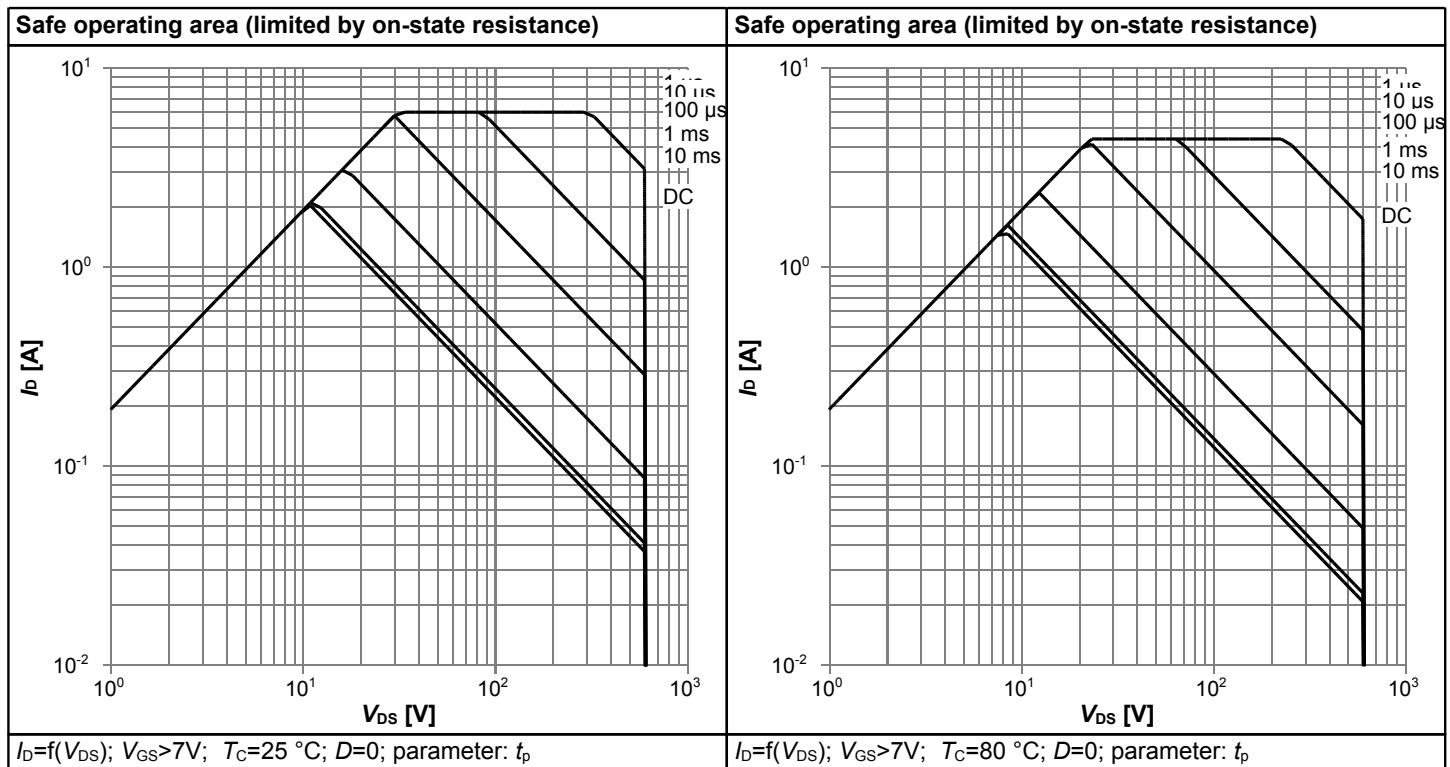
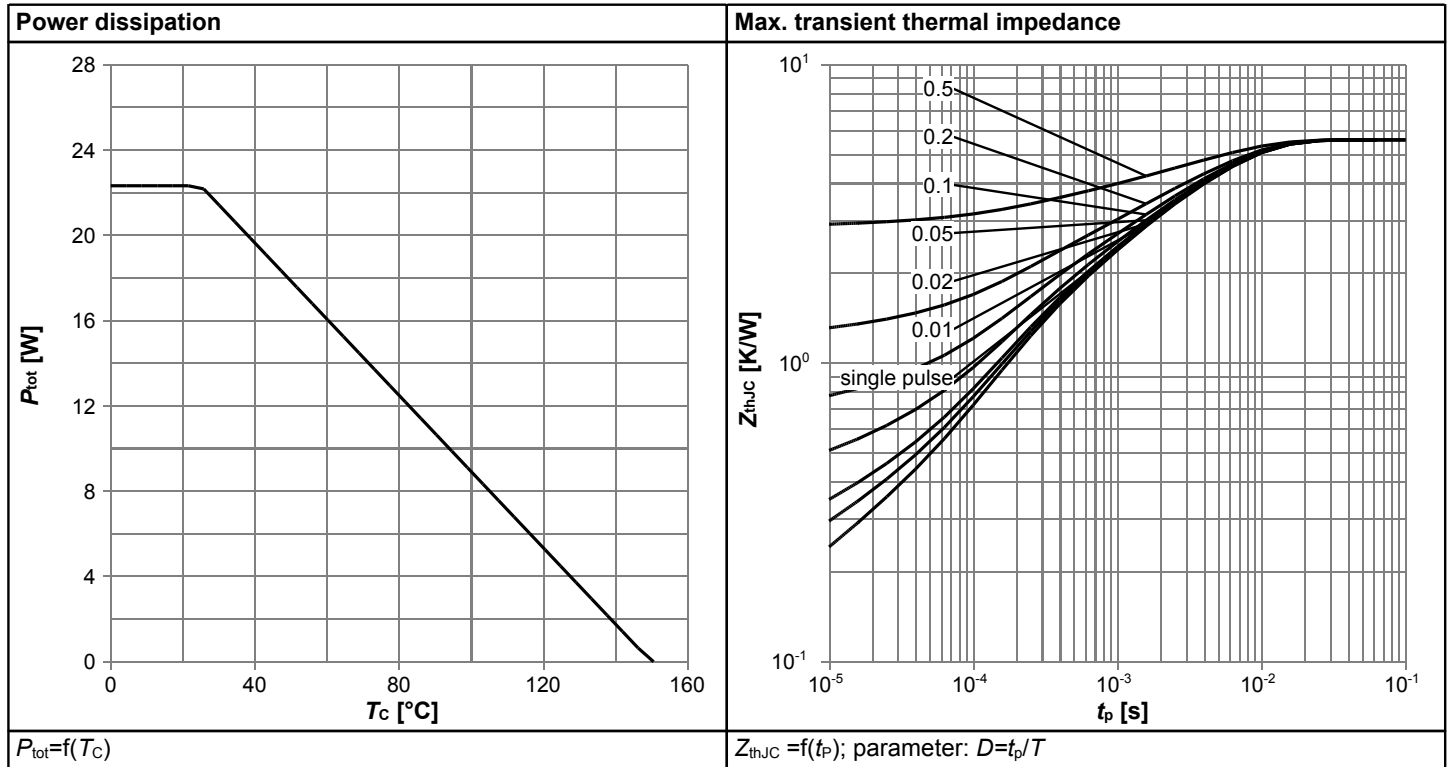
<sup>2)</sup>  $C_{o(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{(BR)DSS}$

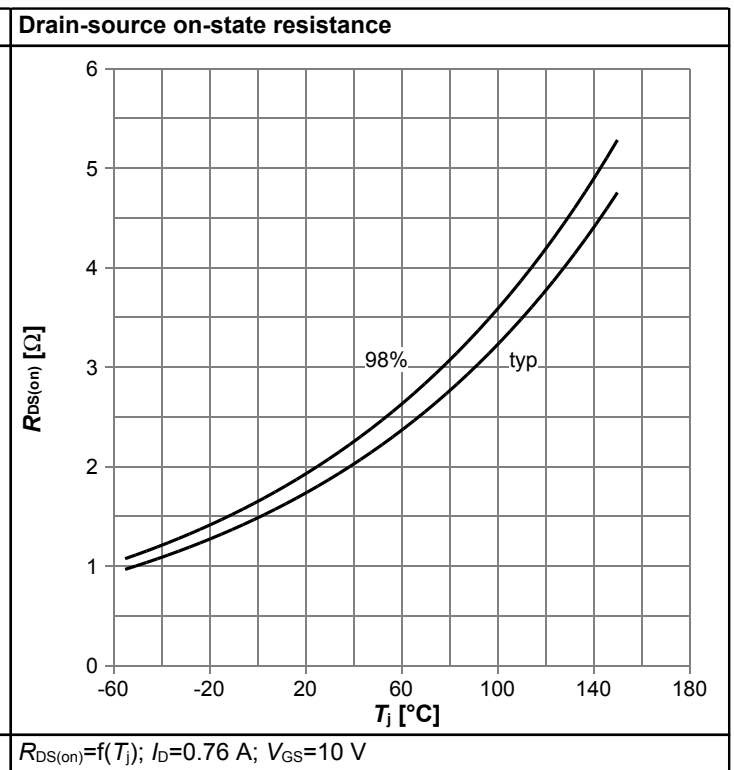
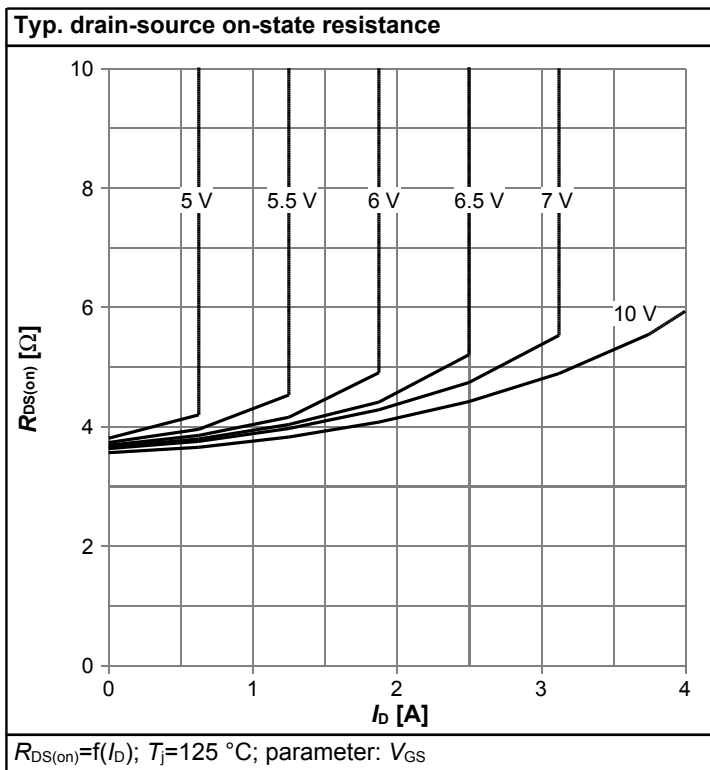
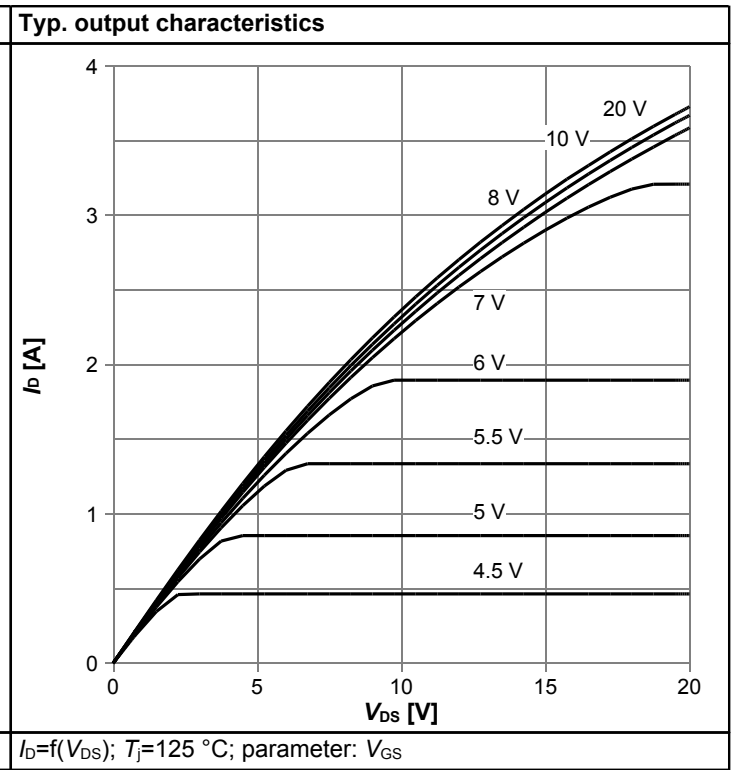
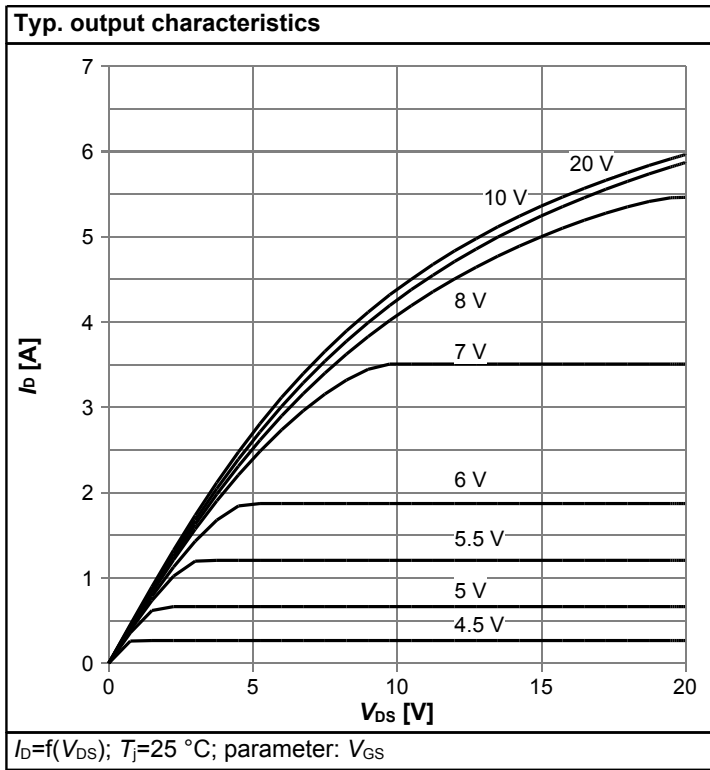
**Table 7 Reverse diode characteristics**

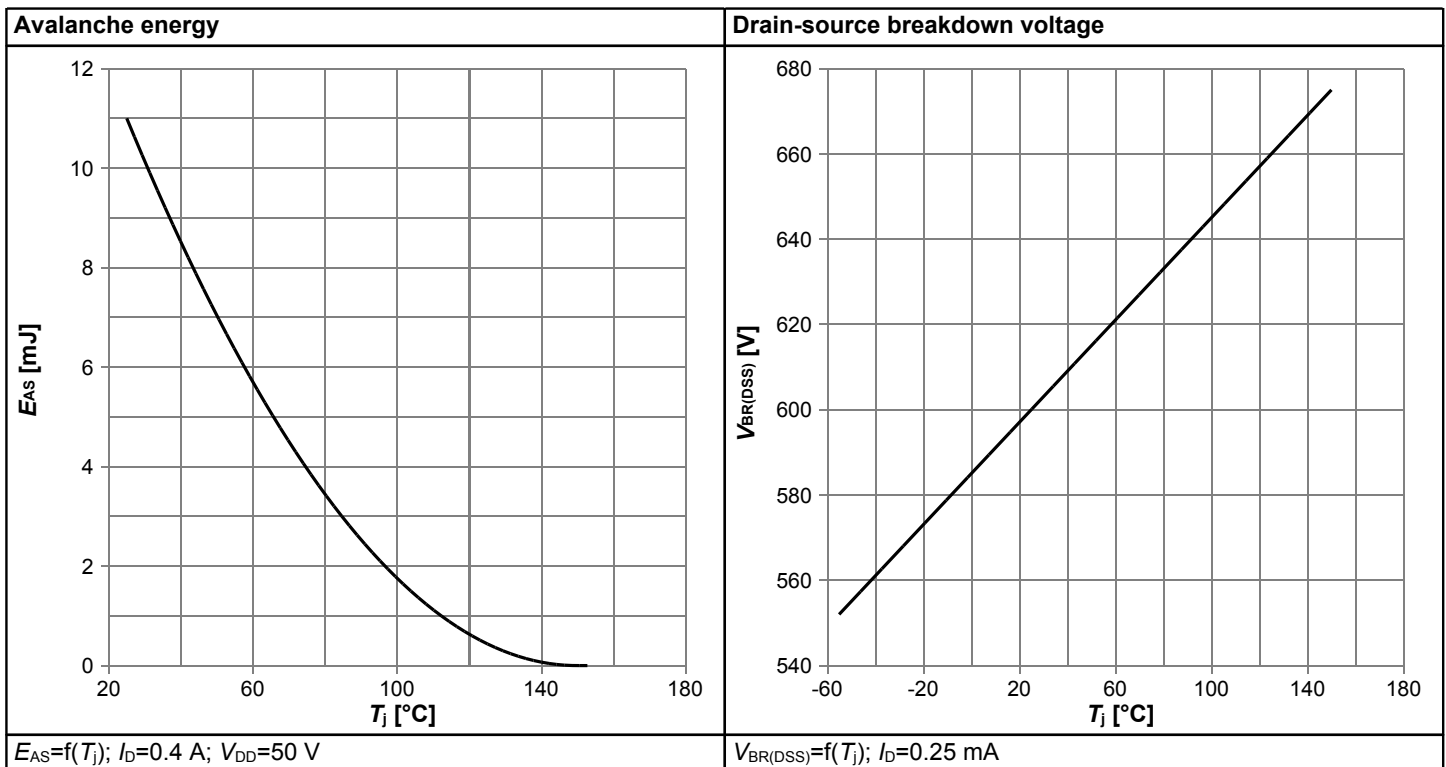
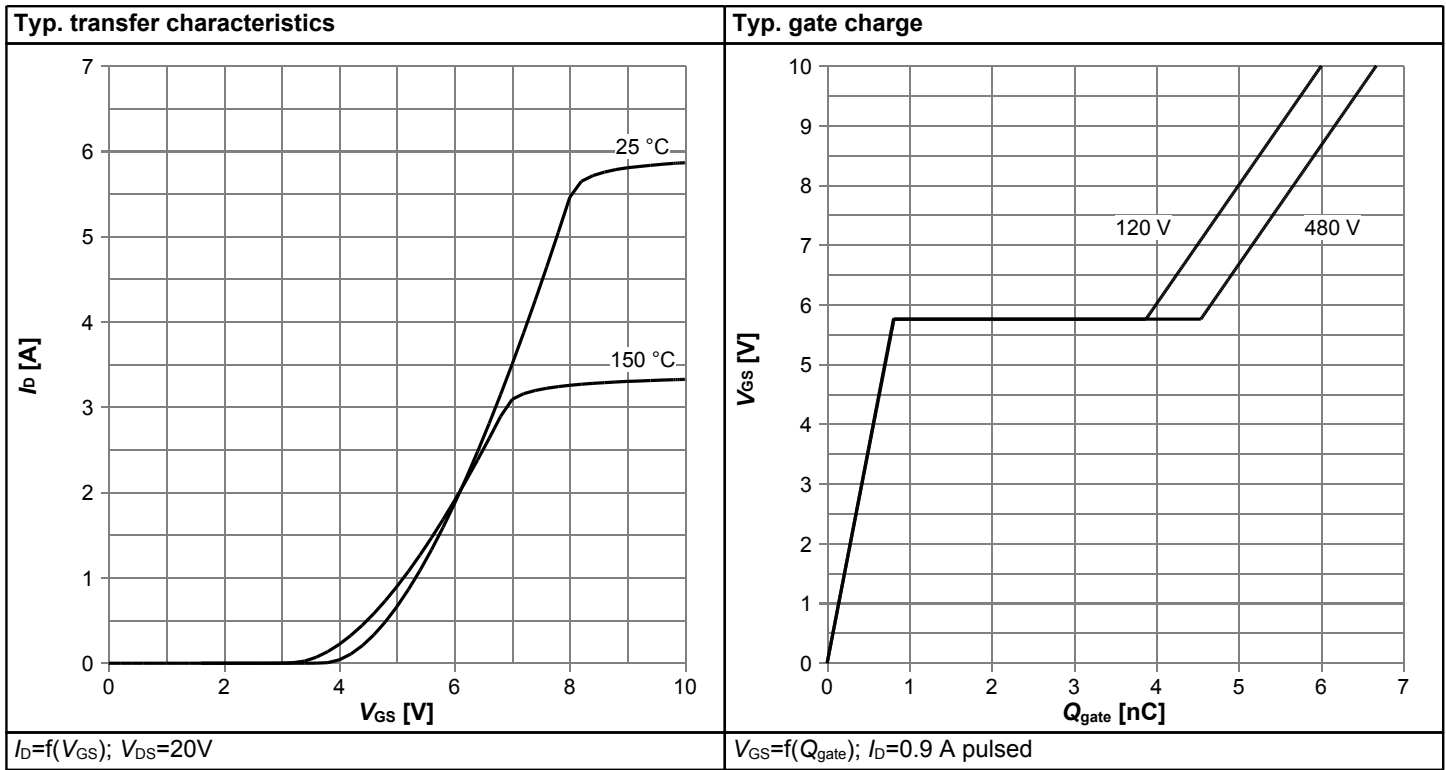
Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	$V_{SD}$		0.9		V	$V_{GS} = 0V, I_F = 0.9A, T_j = 25^\circ C$
Reverse recovery time	$t_{rr}$		180		ns	$V_R = 400V, I_F = 0.9A,$ $di_F/dt = 100A/\mu s$ (see table 8)
Reverse recovery charge	$Q_{rr}$		0.67		$\mu C$	
Peak reverse recovery current	$I_{rrm}$		7.1		A	

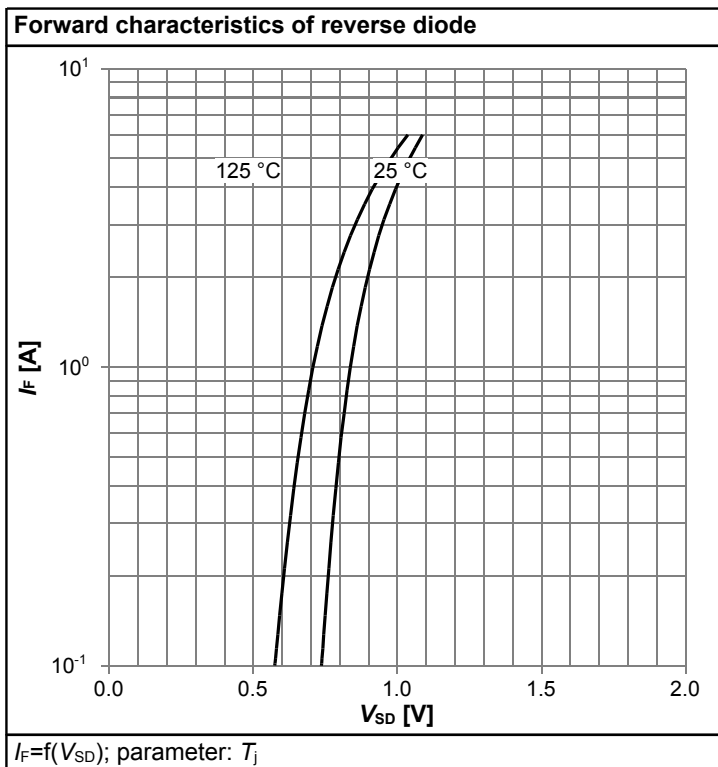
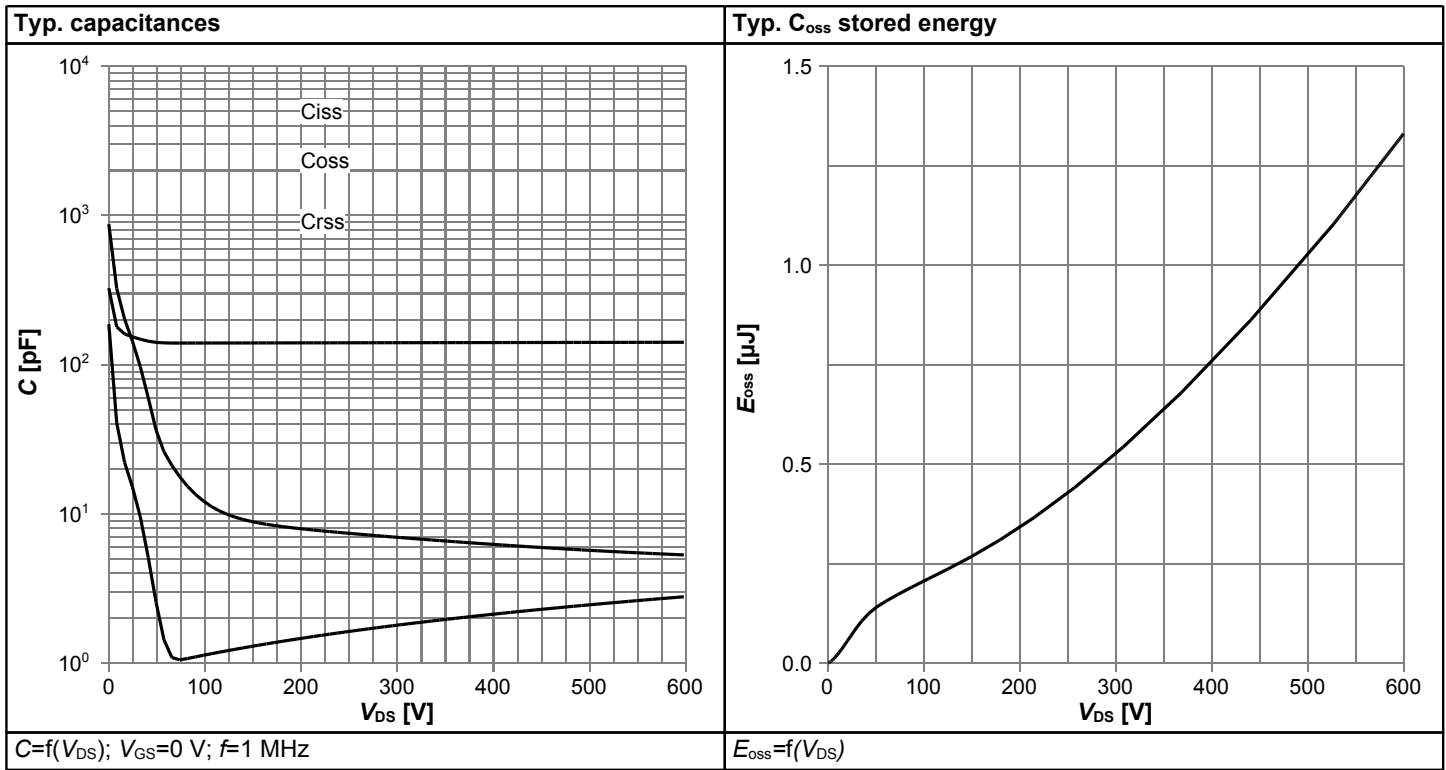


### 5 Electrical characteristics diagrams









## 6 Test Circuits

**Table 8 Diode characteristics**

Test circuit for diode characteristics	Diode recovery waveform

**Table 9 Switching times**

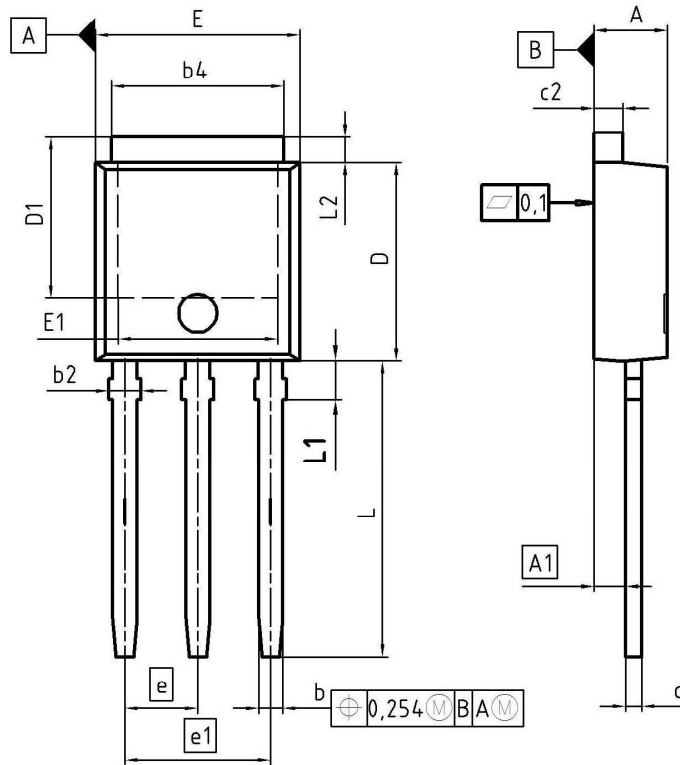
Switching times test circuit for inductive load	Switching times waveform

**Table 10 Unclamped inductive load**

Unclamped inductive load test circuit	Unclamped inductive waveform



## 7 Package Outlines



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.16	2.41	0.085	0.095
A1	0.90	1.14	0.035	0.045
b	0.64	0.89	0.025	0.035
b2	0.65	1.15	0.026	0.045
b4	4.95	5.50	0.195	0.217
c	0.46	0.60	0.018	0.024
c2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	5.04	5.77	0.198	0.227
E	6.35	6.73	0.250	0.265
E1	4.70	5.21	0.185	0.205
e	2.29		0.090	
e1	4.57		0.180	
N	3		3	
L	8.89	9.65	0.350	0.380
L1	1.90	2.29	0.075	0.090
L2	0.89	1.37	0.035	0.054

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Figure 1 Outline PG-TO 251, dimensions in mm/inches

## 8 Appendix A

### Table 11 Related Links

- **IFX C6 Product Brief:** [www.infineon.com](http://www.infineon.com)
- **IFX C6 Portfolio:** [www.infineon.com](http://www.infineon.com)
- **IFX CoolMOS Webpage:** [www.infineon.com](http://www.infineon.com)
- **IFX Design Tools:** [www.infineon.com](http://www.infineon.com)

## Revision History

IPU60R2K0C6

**Revision: 2015-10-09, Rev. 2.2**

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.1	2012-02-02	Final datasheet release
2.2	2015-10-09	Updated with Halogen free information

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